

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A photolithographic process comprising the acts of:

forming a metallic surface on a substrate,

applying a photoresist layer, with a substantially uniform thickness, on a substrate the metallic surface,

locally exposing the photoresist layer to a radiation source with a suitable wavelength,

providing a suitable liquid developer composition on the substrate,

dissolving an exposed or unexposed region of the photoresist layer with the developer composition, and

rinsing and drying the photoresist layer thereby interrupting said dissolving act,

wherein ~~the substrate has a metallic surface in contact with~~
~~the photoresist layer and~~ the photoresist layer has a thickness d_r
< 100nm to improve photoresist wall steepness, and

wherein the metallic surface comprises Ni or Au.

2. (Previously Presented) The photolithographic process as claimed in claim 1, wherein the substrate comprises a metallic surface layer, with a thickness d_m larger than approximately 10nm, and a further substrate material.

Claim 3 (Canceled)

4. (Previously Presented) The photolithographic process as claimed in claim 1, wherein the photoresist is a positive novolac resin-based photoresist.

5. (Previously Presented) The photolithographic process as claimed in claim 1, wherein the substrate is a master substrate for the production of a high density optical medium.

6. (Previously Presented) A stamper for the production of optical data storage media, manufactured by using the master substrate as used in claim 5.

7. (Previously Presented) Use of a stamper as claimed in claim 6 for the manufacture of a high density optical data storage medium.

8. (Previously Presented) An optical data storage medium produced in an injection molding process by using the stamper of claim 6.

9. (Previously Presented) The photolithographic process of claim 1, wherein the photoresist wall steepness is at least 70 degrees.

10. (Previously Presented) The photolithographic process of claim 1, wherein the photoresist wall steepness is at least 65 degrees.

11.(New) The photolithographic process of claim 1, wherein the metallic surface has a thickness of 10nm.